



# TRANSMITTAL FORM

Application Serial Number Filing Date First Named Inventor Group Art Unit Examiner Name Attorney Docket No. Patent No. Issue Date	10/022,689 December 17, 2001 Fitzgerald 2813 Laura M. Schillinger ASC-023DVC2 Not applicable Not applicable
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**ENCLOSURES (check all that apply)**

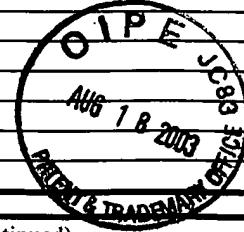
<input checked="" type="checkbox"/> Fee Transmittal Form <ul style="list-style-type: none"> <li><input checked="" type="checkbox"/> Check Attached</li> <li><input type="checkbox"/> Copy of Fee Transmittal Form</li> </ul> <input type="checkbox"/> Amendment/Response <ul style="list-style-type: none"> <li><input type="checkbox"/> Preliminary</li> <li><input type="checkbox"/> After Final</li> <li><input type="checkbox"/> Affidavits/declaration(s)</li> <li><input type="checkbox"/> Letter to Official Draftsperson including Drawings [Total Sheets ____]</li> </ul> <input type="checkbox"/> Petition for Extension of Time	<input type="checkbox"/> Copy of Notice to File Missing Parts of Application <input type="checkbox"/> Formal Drawing(s)	<input type="checkbox"/> Notice of Appeal to Board of Patent Appeals and Interferences <input type="checkbox"/> Appeal Brief (in triplicate)
<input type="checkbox"/> Supplemental Information Disclosure Statement <ul style="list-style-type: none"> <li><input checked="" type="checkbox"/> Form PTO-1449</li> <li><input checked="" type="checkbox"/> Copies of IDS Citations</li> </ul> <input type="checkbox"/> Certified Copy of Priority Document(s)	<input type="checkbox"/> Request For Continued Examination (RCE) Transmittal <input type="checkbox"/> Power of Attorney (Revocation of Prior Powers)	<input type="checkbox"/> Status Inquiry <input checked="" type="checkbox"/> Return Receipt Postcard <input checked="" type="checkbox"/> Certificate of First Class Mailing under 37 C.F.R. 1.8
<input type="checkbox"/> Sequence Listing submission <ul style="list-style-type: none"> <li><input type="checkbox"/> Paper Copy/CD</li> <li><input type="checkbox"/> Computer Readable Copy</li> <li><input type="checkbox"/> Statement verifying identity of above</li> </ul>	<input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Executed Declaration and Power of Attorney for Utility or Design Patent Application	<input type="checkbox"/> Certificate of Facsimile Transmission under 37 C.F.R. 1.8 <input type="checkbox"/> Additional Enclosure(s) (please identify below)
	<input type="checkbox"/> Small Entity Statement <input type="checkbox"/> CD(s) for large table or computer program	
	<input type="checkbox"/> Amendment After Allowance <input type="checkbox"/> Request for Certificate of Correction <ul style="list-style-type: none"> <li><input type="checkbox"/> Certificate of Correction (in duplicate)</li> </ul>	

<b>CORRESPONDENCE ADDRESS</b>  Direct all correspondence to: Patent Administrator Testa, Hurwitz & Thibeault, LLP High Street Tower 125 High Street Boston, MA 02110 Tel. No.: (617) 248-7000 Fax No.: (617) 248-7100	<b>SIGNATURE BLOCK</b>  Respectfully submitted,   Natasha C. Us Attorney for the Applicant Testa, Hurwitz & Thibeault, LLP High Street Tower 125 High Street Boston, MA 02110
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**FEE TRANSMITTAL  
FY 2003**

Complete if Known

Application Serial Number	10/022,689
Filing Date	December 17, 2001
First Named Inventor	Fitzgerald
Group Art Unit	2813
Examiner Name	Laura M. Schillinger
Attorney Docket No.	ASC-023DVC2



<b>METHOD OF PAYMENT</b>		<b>FEE CALCULATION (continued)</b>	
1. <input checked="" type="checkbox"/> Payment Enclosed: <input checked="" type="checkbox"/> Check <input type="checkbox"/> Money Order <input type="checkbox"/> Other		3. ADDITIONAL FEES	
2. <input checked="" type="checkbox"/> The Commissioner is hereby authorized to credit or charge any fee indicated below for this submission to Deposit Account No. 20-0531. <input type="checkbox"/> Required Fees (copy of this sheet enclosed). <input checked="" type="checkbox"/> Additional fee required under 37 CFR 1.16 and 1.17. <input checked="" type="checkbox"/> Overpayment Credit.		Large Entity Fee (\$)	Small Entity Fee (\$)
3. <input type="checkbox"/> Applicant claims small entity status.		Fee Description	Fee Paid
<b>FEE CALCULATION</b>			
1. FILING FEE			
Large Entity			
Fee (\$)	Fee Description	Fee Paid	
750	Utility filing fee		
330	Design filing fee		
160	Provisional filing fee		
Number Filed	Number Extra	Rate	Amount
Total Claims	- 20 =	x \$ 18.00 =	
Independent Claims	- 3 =	x \$ 84.00 =	
<input type="checkbox"/> Multiple Dependent Claim(s), if any		\$280.00 =	
TOTAL:			
SMALL ENTITY DISCOUNT:			
SUBTOTAL (1) (\$)		0.00	
2. AMENDMENT CLAIM FEES			
Claims Remaining After Amend.	Highest No. Previously Paid For	Present Extra	Fee Paid
Total Indep.	- - =	x \$ 18.00 =	
	- - =	x \$ 84.00 =	
<input type="checkbox"/> First Presentation of Multiple Dep. Claim		+ \$280.00 =	
TOTAL:		(\$)	
SMALL ENTITY DISCOUNT:		(\$)	
SUBTOTAL (2) (\$)		0.00	
SUBTOTAL (3) (\$)			
180.00			
SUBTOTAL (1) 0.00			
SUBTOTAL (2) 0.00			
SUBTOTAL (3) 180.00			
TOTAL (\$)			
180.00			
<b>CORRESPONDENCE ADDRESS</b>		<b>SIGNATURE BLOCK</b>	
Direct all correspondence to:  Patent Administrator Testa, Hurwitz & Thibeault, LLP High Street Tower-125 High Street Boston, MA 02110 Tel. No.: (617) 248-7000 Fax No.: (617) 248-7100		Respectfully submitted,   Natasha C. Us Attorney for the Applicant Testa, Hurwitz & Thibeault, LLP High Street Tower-125 High Street Boston, MA 02110	



**PATENT**

Attorney Docket No. ASC-023DVC2

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

APPLICANT(S): Fitzgerald  
SERIAL NO.: 10/022,689 GROUP NO.: 2813  
FILING DATE: December 17, 2001 EXAMINER: Laura M. Schillinger  
TITLE: CONTROLLING THREADING DISLOCATION DENSITIES IN GE  
ON SI USING GRADED GESI LAYERS AND PLANARIZATION

**CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8**

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 13th day of August, 2003.

Olivia J. Mannion  
Olivia J. Mannion

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith are: Transmittal Form (1 page); Fee Transmittal (1 page); Supplemental Information Disclosure Statement (3 pages); Form PTO-1449 (12 pages); References Labeled A1 to A116, B1 to B39 and C1 to C94; Check in the Amount of \$180.00; and a return receipt postcard.

VER 9/00  
2668623-1



PATENT  
Attorney Docket No. ASC-023DVC2

#17 / SUPP  
105  
11-20-03  
et al.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Fitzgerald  
SERIAL NO.: 10/022,689 GROUP NO.: 2813  
FILING DATE: December 17, 2001 EXAMINER: Laura M. Schillinger  
TITLE: CONTROLLING THREADING DISLOCATION DENSITIES IN GE  
ON SI USING GRADED GESI LAYERS AND PLANARIZATION

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed.

08/20/2003 DTESEM1 00000134 10022689

01 FC:1806

180.00 OP

**REMARKS**

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- (1) within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- (2) after the period defined in (1) but before the mailing date of a final action or a notice of allowance under 37 C.F.R. 1.311, and
  - the requisite Statement is below, OR
  - the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or

- (3) after the mailing date of a **final action or notice of allowance** but before the payment of the **issue fee**, AND
- the requisite Statement is below, AND
- the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

In addition, Applicant wishes to inform the Examiner about the following co-pending patent applications, publications, issued patents, and Office Actions issued therein:

U.S. Serial No. 10/264,935, filed on October 4, 2002, by Lochtefeld et al.;

U.S. Serial No. 10/456,708, filed on 06/06/2003, by Lochtefeld et al.;

U.S. Serial No. 10/456,103, filed on 06/06/2003, by Lochtefeld et al.;

U.S. Publication No. 2003-0102498-A1, published 06/05/2003, by Braithwaite et al.;

U.S. Serial No. 10/389,003, filed 03/14/2003, by Fitzgerald;

U.S. Patent No. 6,107,653, issued 08/22/2000, by Fitzgerald;

U.S. Patent No. 6,291,321, issued 09/18/2001, by Fitzgerald;

U.S. Serial No. 09/611,024, filed 07/06/2000, by Fitzgerald;

U.S. Patent No. 6,573,126, issued 06/03/2003, by Cheng et al.;

U.S. Serial No. 10/384,160, filed 03/07/2003, by Cheng et al.;

U.S. Serial No. 10/379,355, filed 03/04/2003, by Cheng et al.;

U.S. Patent No. 6,602,613, issued 08/05/2003, by Fitzgerald;

U.S. Serial No. 10/391,086, filed on 03/18/2003, by Fitzgerald;

U.S. Serial No. 09/764,177, filed on 01/07/2001, by Fitzgerald;

U.S. Publication No. 2002-0100942 A1, published 08/01/2002, by Fitzgerald et al.;

U.S. Publication No. 2002-0125471, published 09/12/2002, by Fitzgerald et al.;

U.S. Publication No. 2003-0034529, published 02/20/2003, by Fitzgerald et al.;

U.S. Serial No. 10/625,018, filed 07/23/2003, by Fitzgerald et al.;

U.S. Publication No. 2002-0123197, published 07/05/2002, by Fitzgerald et al.;

U.S. Serial No. 10/611,739, filed 07/01/2003, by Fitzgerald et al.;

U.S. Publication No. 2002-0125497, published 09/12/2002, by Fitzgerald;

U.S. Serial No. 09/906,545, filed on 07/16/2001, by Fitzgerald;

U.S. Serial No. 09/906,200, filed 07/16/2001, by Fitzgerald; and

U.S. Publication No. 2003-0077867, published 07/24/2003, by Fitzgerald.

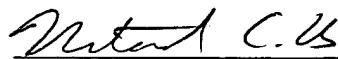
It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: August 13, 2003  
Reg. No. 44,381

Tel. No.: (617) 310-8327  
Fax No.: (617) 248-7100

VER 12/00  
2668576-1



Natasha C. Us  
Attorney for the Applicant  
Testa, Hurwitz, & Thibeault, LLP  
High Street Tower  
125 High Street  
Boston, Massachusetts 02110

<b>FORM PTO - 1449</b>		ATTY DOCKET NO.: ASC-023DVC2
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		APPLICANTS: Fitzgerald
		SERIAL NO.: 10/022,689
		FILING DATE: December 17, 2001
		GROUP: 2813

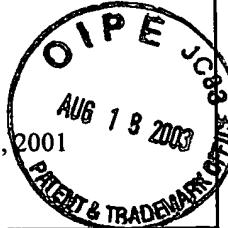


### U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,710,788	12/01/1987	Dambkes et al.			
	A3	4,987,462	01/22/1991	Kim et al.			
	A4	4,990,979	02/05/1991	Otto			
	A5	5,013,681	05/07/1991	Godbey et al.			
	A6	5,155,571	10/13/1992	Wang et al.			
	A7	5,166,084	11/24/1992	Pfiester			
	A8	5,202,284	04/01/1993	Kamins et al.			
	A9	5,207,864	05/04/1993	Bhat et al.			
	A10	5,208,182	05/04/1993	Narayan et al.			
	A11	5,212,110	05/18/1993	Pfiester et al.			
	A12	5,221,413	06/22/1993	Brasen et al.			
	A13	5,241,197	08/31/1993	Murakami et al.			
	A14	5,285,086	02/08/1994	Fitzgerald, Jr.			
	A15	5,291,439	03/01/1994	Kauffmann, et al.			
	A16	5,310,451	05/10/1994	Tejwani et al.			
	A17	5,316,958	05/31/1994	Meyerson			
	A18	5,346,848	09/13/1994	Grupen-Shemansky et al.			
	A19	5,374,564	12/20/1994	Bruel			
	A20	5,413,679	05/09/1995	Godbey			
	A21	5,426,069	06/20/1995	Selvakumar et al.			
	A22	5,426,316	06/20/1995	Mohammad			
	A23	5,461,243	10/24/1995	Ek et al.			
	A24	5,461,250	10/24/1995	Burghartz et al.			
	A25	5,462,883	10/31/1995	Dennard et al.			
	A26	5,476,813	12/19/1995	Naruse			
	A27	5,479,033	12/26/1995	Baca et al.			
	A28	5,484,664	01/16/1996	Kitahara et al.			
	A29	5,523,243	06/04/1996	Mohammad			
	A30	5,523,592	06/04/1996	Nakagawa et al.			

EXAMINER	DATE CONSIDERED
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<b>FORM PTO - 1449</b>		ATTY DOCKET NO.: ASC-023DVC2
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		APPLICANTS: Fitzgerald
		SERIAL NO.: 10/022,689
		FILING DATE: December 17, 2001
		GROUP: 2813

**U.S. PATENT DOCUMENTS**

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A31	5,536,361	07/16/1996	Kondo et al.			
	A32	5,540,785	07/30/1996	Dennard et al.			
	A33	5,596,527	01/12/1997	Tomioka, et al.			
	A34	5,617,351	04/01/1997	Bertin, et al.			
	A35	5,683,934	11/04/1997	Candelaria			
	A36	5,698,869	12/16/1997	Yoshimi et al.			
	A37	5,728,623	03/17/1998	Mori			
	A38	5,739,567	04/14/1998	Wong			
	A39	5,759,898	06/02/1998	Ek et al.			
	A40	5,777,347	07/07/1998	Bartelink			
	A41	5,786,612	07/28/1998	Otani et al.			
	A42	5,786,614	07/28/1998	Chuang, et al.			
	A43	5,792,679	08/11/1998	Nakato			
	A44	5,808,344	09/15/1998	Ismail et al.			
	A45	5,847,419	12/08/1998	Imai et al.			
	A46	5,877,070	03/02/1999	Goesele et al.			
	A47	5,906,708	05/25/1999	Robinson et al.			
	A48	5,912,479	06/15/1999	Mori et al.			
	A49	5,943,560	08/24/1999	Chang et al.			
	A50	5,963,817	10/05/1999	Chu et al.			
	A51	5,966,622	10/12/1999	Levine et al.			
	A52	5,998,807	12/07/1999	Lustig et al.			
	A53	6,013,134	01/11/2000	Chu et al.			
	A54	6,033,974	03/07/2000	Henley et al.			
	A55	6,033,995	03/07/2000	Muller			
	A56	6,058,044	05/02/2000	Sugiura et al.			
	A57	6,074,919	06/13/2000	Gardner et al.			
	A58	6,096,590	08/01/2000	Chan et al.			
	A59	6,103,559	08/15/2000	Gardner et al.			
	A60	6,111,267	08/29/2000	Fischer et al.			

**EXAMINER****DATE CONSIDERED**

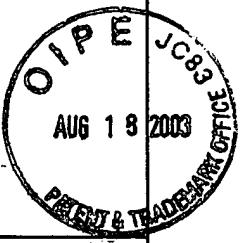
<b>FORM PTO - 1449</b>		ATTY DOCKET NO.: ASC-023DVC2
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		APPLICANTS: Fitzgerald
		SERIAL NO.: 10/022,689
		FILING DATE: December 17, 2000
		GROUP: 2813

**U.S. PATENT DOCUMENTS**

<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>
	A61	6,117,750	09/12/2000	Bensahel et al.			
	A62	6,130,453	10/10/2000	Mei, et al.			
	A63	6,133,799	10/17/2000	Favors, Jr., et al.			
	A64	6,140,687	10/31/2000	Shimomura et al.			
	A65	6,143,636	11/07/2000	Forbes, et al.			
	A66	6,153,495	11/28/2000	Kub et al.			
	A67	6,154,475	11/28/2000	Soref et al.			
	A68	6,160,303	12/12/2000	Fattaruso			
	A69	6,162,688	12/19/2000	Gardner et al.			
	A70	6,184,111	02/06/2001	Henley et al.			
	A71	6,191,007	02/20/2001	Matsui et al.			
	A72	6,191,432	02/20/2001	Sugiyama et al.			
	A73	6,194,722	02/27/2001	Fiorini et al.			
	A74	6,204,529	03/20/2001	Lung, et al.			
	A75	6,207,977	03/01/2001	Augusto			
	A76	6,210,988	04/03/2001	Howe et al.			
	A77	6,218,677	04/17/2001	Broekaert			
	A78	6,232,138	05/15/2001	Fitzgerald et al.			
	A79	6,235,567	05/22/2001	Huang			
	A80	6,242,324	06/05/2001	Kub et al.			
	A81	6,249,022	06/19/2001	Lin, et al.			
	A82	6,251,755	06/26/2001	Furukawa et al.			
	A83	6,261,929	07/01/2001	Gehrke et al.			
	A84	6,266,278	07/24/2001	Harari, et al.			
	A85	6,271,551	08/07/2001	Schmitz et al.			
	A86	6,271,726	08/07/2001	Fransis et al.			
	A87	6,313,016	11/06/2001	Kibbel et al.			
	A88	6,316,301	11/13/2001	Kant			
	A89	6,323,108	11/27/2001	Kub et al.			
	A90	6,329,063	12/11/2001	Lo et al.			

<b>EXAMINER</b>	<b>DATE CONSIDERED</b>
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<b>FORM PTO - 1449</b>		ATTY DOCKET NO.: ASC-023DVC2
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		APPLICANTS: Fitzgerald
		SERIAL NO.: 10/022,689
		FILING DATE: December 17, 2001
		GROUP: 2813

**U.S. PATENT DOCUMENTS**

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A91	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A92	6,339,232	01/15/2002	Takagi			09/20/1999
	A93	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A94	6,372,356	04/16/2002	Thornton et al.			04/028/2000
	A95	6,399,970	06/04/2002	Kubo et al.			09/16/1997
	A96	6,407,406	06/18/2002	Tezuka			06/29/1999
	A97	6,425,951	07/30/2002	Chu et al.			08/06/1999
	A98	6,429,061	08/06/2002	Rim			07/26/2000
	A99	6,420,937	07/16/2002	Akatsuka et al.			06/14/2001
	A100	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A101	6,555,839	04/29/2003	Fitzgerald			05/16/2001
	A102	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A103	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A104	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
	A105	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
	A106	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A107	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A108	2002/0096717	07/25/2002	Chu et al.			01/25/2001
	A109	2002/0100942	08/01/2001	Fitzgerald et al.			06/19/2001
	A110	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A111	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
	A112	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A113	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A114	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A115	6,603,156	08/05/2003	Rim			03/31/2001
	A116	2003/0003679	01/02/2003	Doyle et al.			06/29/2001

EXAMINER	DATE CONSIDERED
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<b>FORM PTO - 1449</b>		ATTY DOCKET NO.:	ASC-023DVC2
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>		APPLICANTS:	Fitzgerald
		SERIAL NO.:	10/022,689
		FILING DATE:	December 17, 2001
		GROUP:	2813


**FOREIGN PATENT DOCUMENTS**

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				NO	NO
	B2	0 587 520	03/16/1994	EP				NO	YES
	B3	0 683 522	11/22/1995	EP				NO	YES
	B4	0 828 296	03/11/1998	EP				NO	YES
	B5	0 829 908	03/18/1998	EP				NO	YES
	B6	0 838 858	04/29/1998	EP				NO	NO
	B7	1 020 900	07/19/2000	EP				NO	YES
	B8	1 174 928	01/23/2002	EP				NO	YES
	B9	2 342 777	04/19/2000	GB				YES	YES
	B10	10-270685	10/09/1998	JP				NO	YES
	B11	11-233744	08/27/1999	JP				NO	NO
	B12	2000-021783	08/31/2000	JP				NO	YES
	B13	2000-031491	01/28/2000	JP				NO	NO
	B14	2001-319935	11/16/2001	JP				NO	YES
	B15	2002-076334	03/15/2002	JP				NO	YES
	B16	2002-164520	06/07/2002	JP				NO	YES
	B17	2002-289533	10/04/2002	JP				NO	YES
	B18	4-307974	10/30/1992	JP				NO	NO
	B19	5-166724	07/02/1993	JP				NO	Abstract Only
	B20	6-177046	06/24/1994	JP				NO	Abstract Only
	B21	7-106446	04/21/1995	JP				NO	NO
	B22	7-240372	09/12/1995	JP				NO	Abstract Only
	B23	00/48239	08/17/2000	WO				NO	YES
	B24	00/54338	09/14/2000	WO				NO	YES

EXAMINER	DATE CONSIDERED
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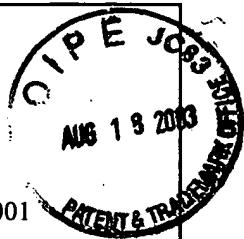


#### FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B25	01/022482	03/29/2001	WO				NO	YES
	B26	01/54202	07/26/2001	WO				NO	YES
	B27	01/93338	12/06/2001	WO				NO	YES
	B28	01/99169	12/27/2001	WO				NO	YES
	B29	02/071488	09/12/2002	WO				NO	YES
	B30	02/071491	09/12/2002	WO				NO	YES
	B31	02/071495	09/12/2002	WO				NO	YES
	B32	02/082514	10/17/2002	WO				NO	YES
	B33	02/13262	02/14/2002	WO				NO	YES
	B34	02/15244	02/21/2002	WO				NO	YES
	B35	02/27783	04/04/2002	WO				NO	YES
	B36	02/47168	06/13/2002	WO				NO	YES
	B37	98/59365	12/30/1998	WO				NO	YES
	B38	99/53539	10/21/1999	WO				NO	YES
	B39	6-252046	11/19/1992	JP				NO	YES

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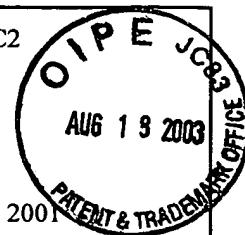
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